

Docket No.: 300.1158

Serial No. 10/827,318

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please AMEND claims 1-4 and ADD new claims 5-8 in accordance with the following:

1. (CURRENTLY AMENDED) A semiconductor device substrate comprised of a core substrate on ~~at least one surface~~ both main surfaces of which interconnect patterns are formed via ~~a resin layer~~, wherein:

the core substrate is formed by a material having a heat expansion coefficient closer to ~~that of a semiconductor chip~~ than those of the main resin layers and the interconnect patterns inside the substrate, ~~;~~ and

a resin layer, forming an outermost layer of the substrate on each of the main surfaces thereof, is formed using of a material having at least one of a higher strength and a higher elongation than a resin material used for inner resin layers in the substrate, thereby preventing cracking, deformation, and other problems arising in the substrate due to the thermal stress occurring between the core substrate and the inner resin layers in the substrate and interconnect patterns ~~being prevented in the substrate~~.

2. (CURRENTLY AMENDED) ~~A~~ The semiconductor device substrate as set forth in claim 1, wherein a further resin layer, under ~~a the resin layer~~ forming ~~an the~~ outermost layer of the substrate, is made of a resin material having at least one of a higher strength and higher elongation than the resin material of ~~a the inner resin layers used further inside in the substrate~~.

3. (CURRENTLY AMENDED) ~~A~~ The semiconductor device substrate as set forth in claim 1, wherein the resin material forming the outermost layer has ~~having at least one of a higher strength and higher elongation~~ is a resin material having a fracture strength of at least 90 MPa and elongation of at least 10%.

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4. (CURRENTLY AMENDED) ~~A~~The semiconductor device substrate as set forth in claim 2, wherein the resin material forming the outermost layer has ~~having at least one of a higher strength and higher elongation is a resin material having a~~ fracture strength of at least 90 MPa and elongation of at least 10%.

5. (NEW) A semiconductor device substrate, comprising:
a core substrate on both main surfaces of which interconnect patterns are formed via resin layers;
a core substrate of a material having a heat expansion coefficient closer to that of a semiconductor chip than those of resin layers and interconnect patterns inside the substrate;
and
a resin layer, of a material having a least one of a higher strength and a higher elongation than a resin material used for the resin layers inside the substrate, forming an outermost layer on each of the opposite main surfaces of the substrate.

6. (NEW) The semiconductor device substrate as set forth in claim 5, wherein a further resin layer, under the resin layer forming the outermost layer of the substrate, is made of a resin material having at least one of a higher strength and higher elongation than the resin material of the inner resin layers in the substrate.

7. (NEW) The semiconductor device substrate as set forth in claim 5, wherein the resin material forming the outermost layer has a fracture strength of at least 90 MPa and elongation of at least 10%.

8. (NEW) The semiconductor device substrate as set forth in claim 6, wherein the resin material forming the outermost layer has a fracture strength of at least 90 MPa and elongation of at least 10%.